



Dual P-Channel 2.5-V (G-S) MOSFET

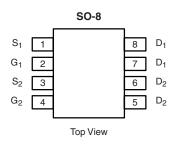
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
- 20	0.032 at $V_{GS} = -4.5 \text{ V}$	- 6.5		
	0.050 at V _{GS} = - 2.5 V	- 5.2		

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Compliant to RoHS Directive 2002/95/EC

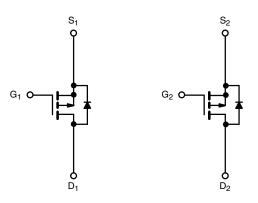






Ordering Information: Si4963BDY-T1-E3 (Lead (Pb)-free)

Si4963BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	A = 25 °C, unle	ss otherwise n	noted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 20		V	
Gate-Source Voltage		V _{GS}	± 12			
Continuous Dunin Comment /T 450 °C\d	T _A = 25 °C	1	- 6.5	- 4.9		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	l _D	- 5.2	- 3.9		
Pulsed Drain Current		I _{DM}	- 40		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	- 1.7	- 0.9		
	T _A = 25 °C	P _D	2.0	1.1	W	
Maximum Power Dissipation ^a	T _A = 70 °C	l _L D	1.3	0.7	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55	to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manifestory London La Auglianda	t ≤ 10 s	B	58	62.5		
Maximum Junction-to-Ambient ^a	Steady State	R _{thJA}	91	110	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	34	40		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm.

Vishay Siliconix



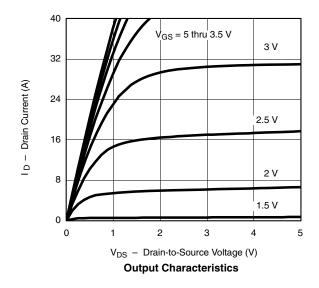
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	nbol Test Conditions Mi		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.6		- 1.4	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA	
Zava Cata Valtaga Drain Current	1	V _{DS} = - 20 V, V _{GS} = 0 V		-1			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 5	μΑ	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 20			Α	
	D	V _{GS} = - 4.5 V, I _D = - 6.5 A		0.025	0.032	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 2 A		0.040	0.050	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 6.5 A		18		S	
Diode Forward Voltage ^a	V _{SD}	I _S = - 1.7 A, V _{GS} = 0 V		- 0.75	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Q_g			14	21		
Gate-Source Charge	Q_{gs}	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -6.5 \text{ A}$		2.6		nC	
Gate-Drain Charge	Q _{gd}			4.6			
Gate Resistance	R _g	f = 1 MHz		8.3		Ω	
Turn-On Delay Time	t _{d(on)}			30	45		
Rise Time	t _r	V_{DD} = - 10 V, R_L = 10 Ω		40	60		
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		80	120	ns	
Fall Time	t _f			55	85		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.7 A, dl/dt = 100 A/μs		40	80		

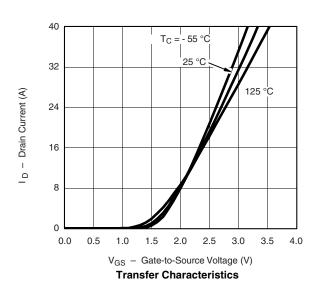
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



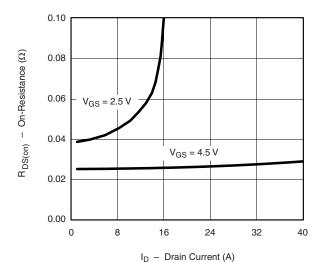




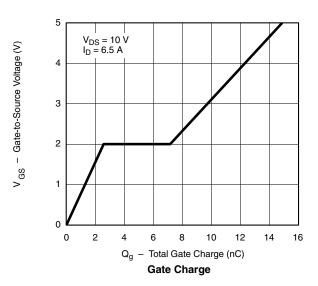


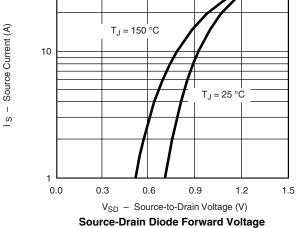


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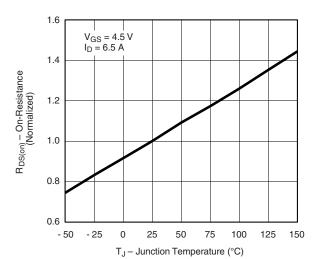
On-Resistance vs. Drain Current



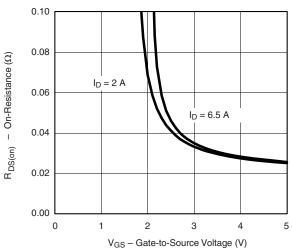


2000 | 1600 | C_{iss} | C_{iss} | C_{oss} | C_{rss} | C_{oss} | C_{oss}

V_{DS} - Drain-to-Source Voltage (V) **Capacitance**



On-Resistance vs. Junction Temperature



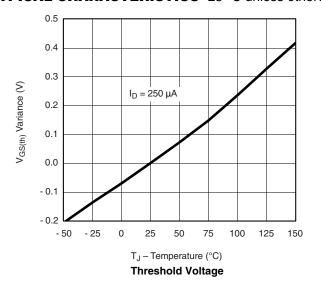
On-Resistance vs. Gate-to-Source Voltage

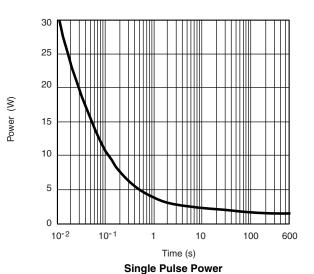
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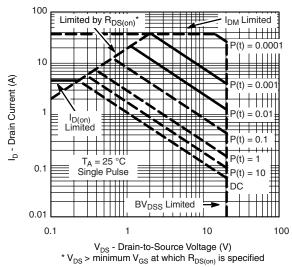
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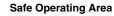
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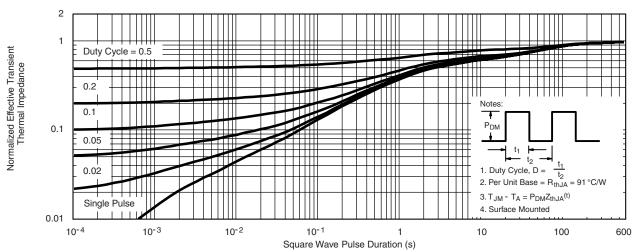
TYPICAL CHARACTERISTICS 25 °C unless otherwise noted







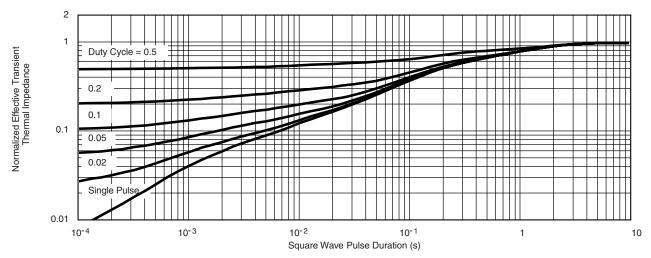




Normalized Thermal Transient Impedance, Junction-to-Ambient



TYPICAL CHARACTERISTICS 25 °C unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg272753.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INCHES		
DIM	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
Е	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I. 11-Sep-06					

DWG: 5498

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

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